

Amendments to the specification

1) page 29, please replace the existing ABSTRACT:

~~A new method is provided for the removal of solvents from exposed surfaces after an etch stop layer has been removed. Exposed surface are treated with a first plasma etch followed by a DI water rinse after which a second plasma etch of exposed surfaces is performed. By selecting the chemistry and the conditions for the first and the second plasma etch, polymer residues and formed copper oxide residues are removed from exposed surfaces.~~

with the following amended ABSTRACT:

A new method is provided for the removal of ~~solvents~~ polymer, possibly mixed with copper oxide residue, from exposed surfaces after an etch stop layer has been removed. ~~Exposed surface~~ The exposed surfaces are treated with a first plasma etch followed by a DI water rinse after which a second plasma etch of the exposed surfaces is performed. By selecting the chemistry and the conditions for the first and the second plasma etch, polymer residues and formed copper oxide residues are removed from the exposed surfaces.

Appl. No. 10/005,803
Amdt. dated 12/03/03
Reply to Office Action of 11/19/03

2) page 5, last paragraph, page 6, first paragraph, please replace the paragraph with the following amended paragraph:

In accordance with the objectives of the invention a new method is provided for the removal of ~~solvents~~ polymers, possibly mixed with copper oxide residue, from exposed surfaces after an etch stop layer has been removed. The exposed surfaces are treated with a first plasma etch followed by a DI water rinse after which a second plasma etch of the exposed surfaces is performed. By selecting the chemistry and the conditions for the first and the second plasma etch, polymer residues and formed copper oxide residues are removed from the exposed surfaces.

3) page 5, second and third paragraph, please replace this text with the following amended text:

A principle objective of the invention is to remove ~~solvents~~ polymers, possibly mixed with copper oxide residue, from semiconductor surfaces.

Another objective of the invention is to enable ~~the use of solvent~~ the removal of polymers, possibly mixed with copper

Appl. No. 10/005,803

Amdt. dated 12/03/03

Reply to Office Action of 11/19/03

oxide residue, without detrimental effects ~~for the removal of~~

~~polymers from~~ on exposed semiconductor surfaces.

4) page 7, second paragraph, please replace this text with the following amended text:

Fig. 5a through 5d show depositions of polymers and the removal of ~~solvents~~ polymers, possibly mixed with copper oxide residue, from exposed surfaces of a via opening.